

Supporting Information

Bidirectional tuning of phase transition properties in Pt: VO₂ nanocomposite thin films

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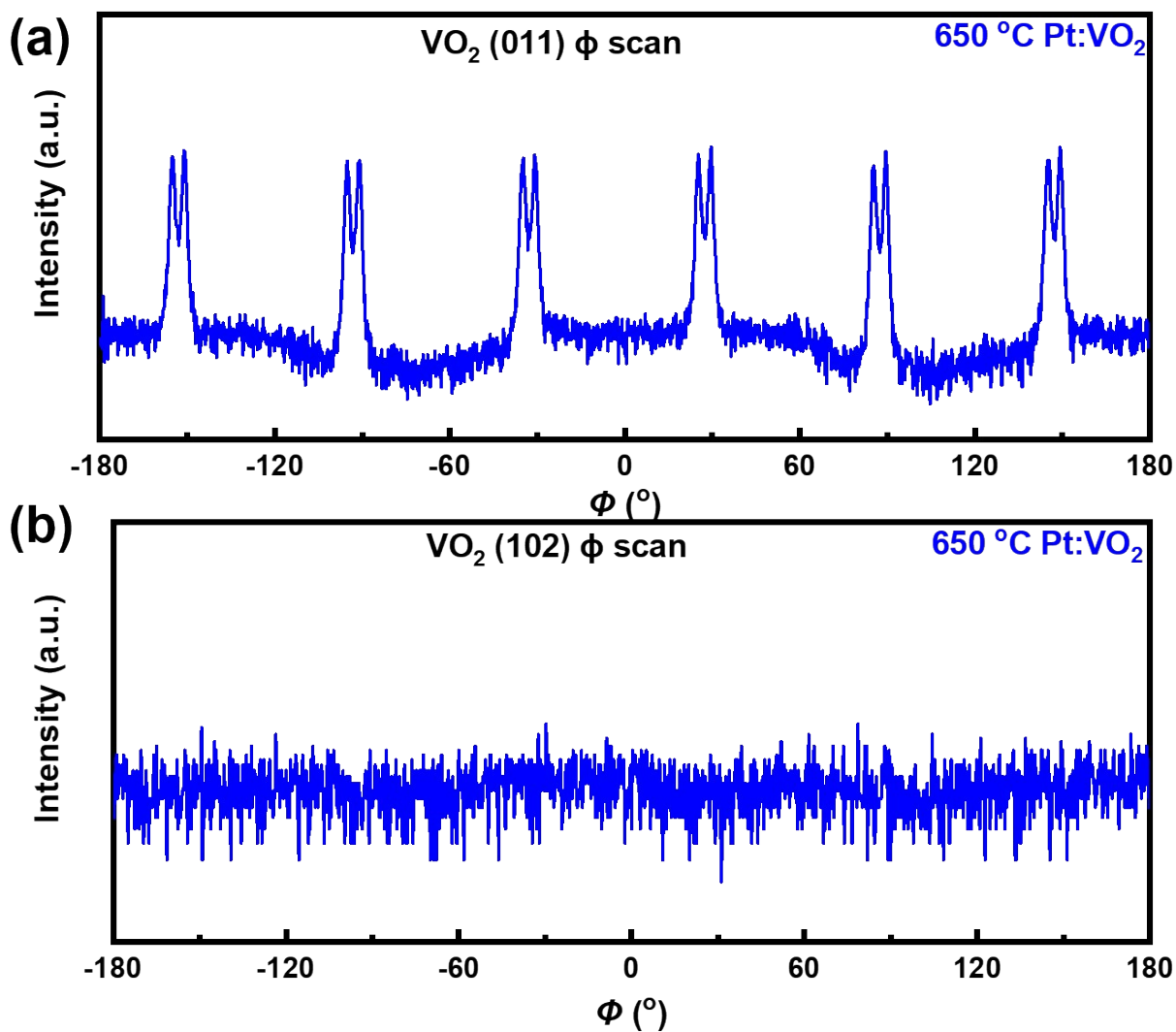


Figure S1. XRD ϕ -scans of (a) (011) plane and (b) (102) plane of Pt: VO₂ nanocomposite thin film deposited at 650 °C.

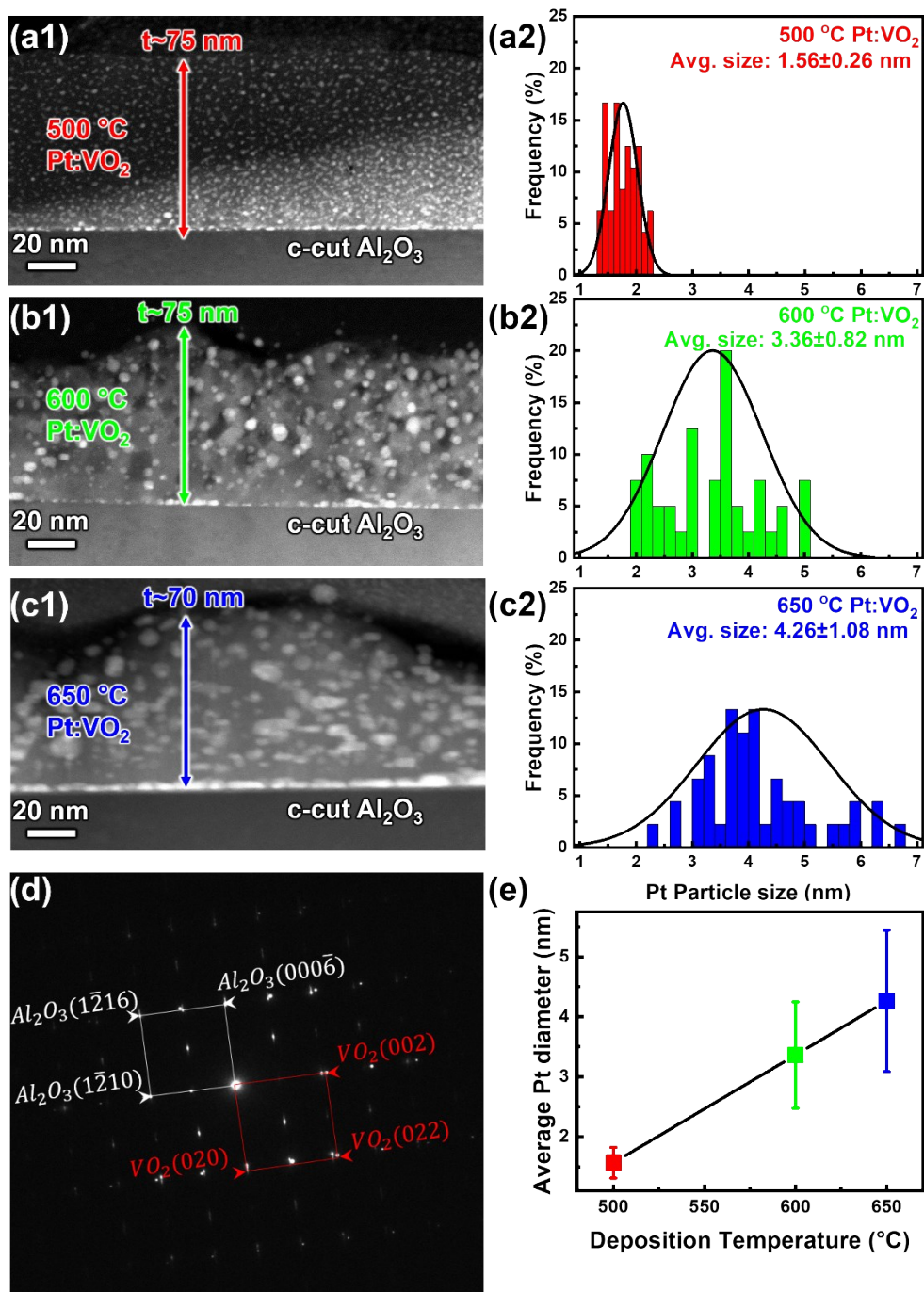


Figure S2. (a1, b1, c1) STEM cross-section images of the Pt: VO₂ nanocomposite thin films deposited at 500, 600, and 650 °C, respectively. (a2, b2, c2) The corresponding Pt NPs size distributions in all Pt: VO₂ nanocomposite thin films. (d) SAED pattern of the film and the substrate along the c-cut sapphire [10 $\bar{1}$ 0] zone for the 500 °C deposited Pt: VO₂ films. (e)

Relationship between average Pt NP size and the corresponding deposition temperatures. Average Pt NP size becomes larger at higher deposition temperature.

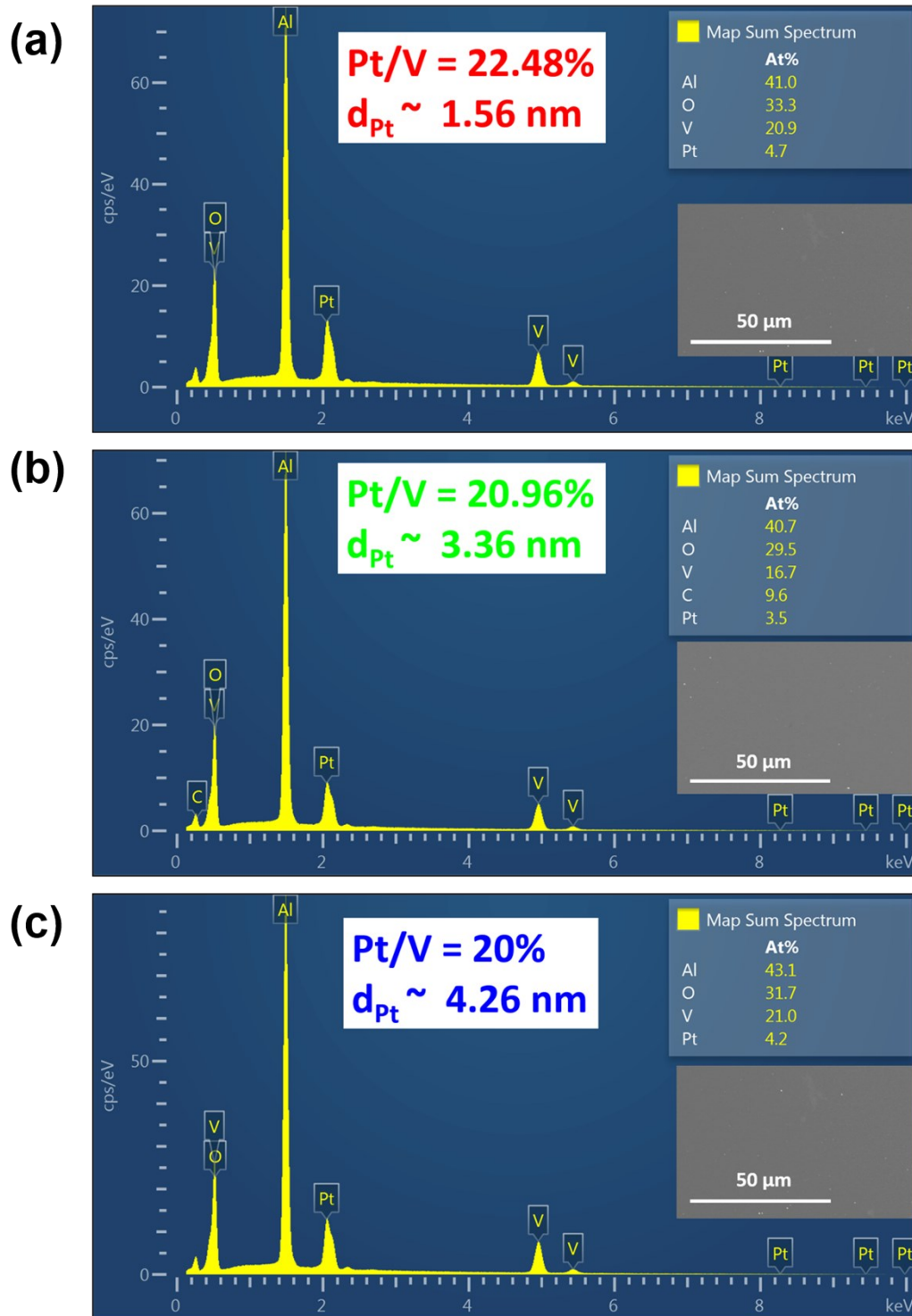


Figure S3. SEM-EDS mapping of the Pt/V atomic ratio in the Pt: VO₂ nanocomposite thin films with the average Pt NP diameter of (a) 1.56 nm, (b) 3.36 nm, and (c) 4.26 nm. The Pt/V atomic ratio is similar for all films.

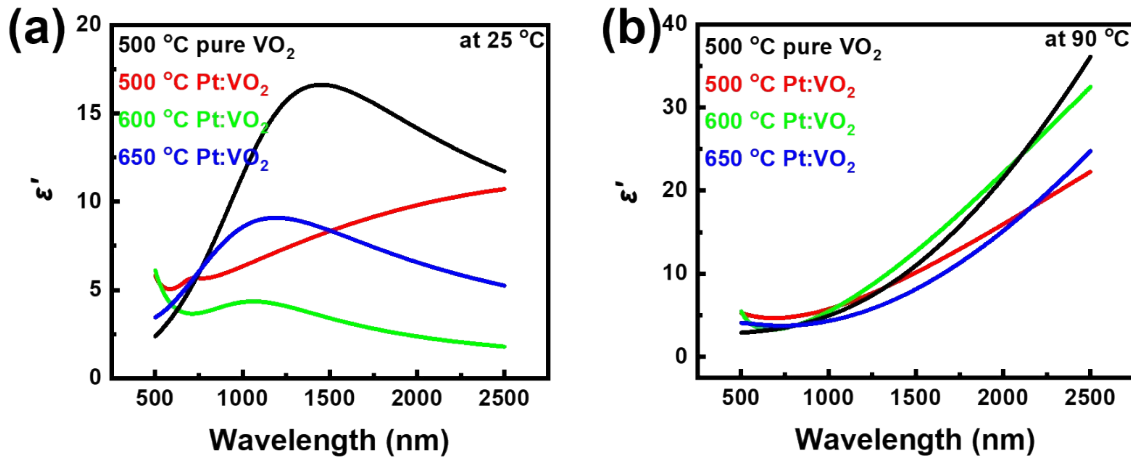


Figure S4. The imaginary part of dielectric permittivity ϵ'' (a) at 25 °C and (b) at 90 °C for Pt: VO₂ nanocomposite thin films deposited at 500, 600, and 650 °C, respectively.